

**Amendments to the Specification:**

Please replace the paragraph on page 3, lines 17-26, of the present application, as filed, with the following amended paragraph:

Further, as conventional technology, there is a disclosure of a “manufacturing method of a semiconductor device”, and technology is described for where a layer of an amorphous alloy with a metal selected from a group consisting of titanium Ti, zirconium Zr, tantalum Ta, molybdenum Mo, niobium Nb, hafnium Hf, and tungsten W is deposited on a surface as a layer containing cobalt Co or nickel [N] Ni in order to prevent the short-circuit caused by the overgrowth upon forming salicide. Here, although there are Examples that show a cobalt content of 50 to 75at% and Ni40Zr60, the alloy content is large for making an amorphous layer (c.f. Japanese Patent Laid-Open Publication No. H5-94966).